Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 – 12. (cancelled)

13. (currently amended): A chemical mechanical polishing method, comprising simultaneously removing by polishing a conductive layer, a silicon oxide layer and a silicon nitride layer using a polishing slurry comprising an abrasive, deionized water, a pH controlling agent, a choline derivative, and polyethylene imine having a molecular structure of $[-CH_2CH_3N(CH_2CH_2NH_2)-]_x[-CH_2CH_2NH_2-]_y$, where one of x and y is a positive integer, and the other of x and y is 0 or a positive integer ~~are 0 or positive integers~~.

14. (currently amended): The method of claim 13, wherein the silicon oxide layer is one selected from the group consisting of a ~~borophosposilicate~~ borophosphorosilicate glass (BPSG), a ~~phosphoresilicate~~ phosphosilicate glass (PSG), a borosilicate glass (BSG), a high density plasma (HDP) silicon oxide layer, an undoped silicate glass (USG), a high thermal (HT)-USG, and a plasma enhanced (PE)-silicon oxide layer.

15. (original): The method of claim 13, wherein the silicon nitride layer is a dielectric material having a basic formula of Si_3N_4.

16. (original): The method of claim 13, wherein the polyethylene imine comprises more than 0.02 wt% of the polishing slurry.

17. (cancelled)

18. (currently amended): The method of claim ~~17~~ 13, wherein the choline derivative is choline chloride.

19. (currently amended): The method of claim ~~17~~ 13, wherein the choline derivative is one selected from the group consisting of choline chloride, choline base, choline bromide, choline iodide, choline dihydrogen citrate, choline bitartrate, choline bicarbonate, choline citrate, choline ascobate, choline borate, choline theophyllinate, choline gluconate, acetylcholine chloride, acetylcholine bromide, and methacholine chloride.

20. (cancelled)

21. (new): The method of claim 13, where both of x and y are positive integers.